

BTA16-600CW3G, BTA16-800CW3G

Triacs Silicon Bidirectional Thyristors

Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

Features

- Blocking Voltage to 800 V
- On-State Current Rating of 16 A RMS at 25°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dV/dt – 1000 V/μs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating dI/dt – 8.5 A/ms minimum at 125°C
- Internally Isolated (2500 V_{RMS})
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|--|--|--------------------|
| Peak Repetitive Off-State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) BTA16-600CW3G BTA16-800CW3G | V _{DRM} , V _{RRM} | 600 800 | V |
| On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T _C = 25°C) | I _{T(RMS)} | 16 | A |
| Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _C = 25°C) | I _{TSM} | 170 | A |
| Circuit Fusing Consideration (t = 10 ms) | I ² t | 144 | A ² sec |
| Non-Repetitive Surge Peak Off-State Voltage (T _J = 25°C, t = 10ms) | V _{DSM} / V _{RSM} | V _{DSM} /V _{RSM} +100 | V |
| Peak Gate Current (T _J = 125°C, t = 20 μs) | I _{GM} | 4.0 | A |
| Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 80°C) | P _{GM} | 20 | W |
| Average Gate Power (T _J = 125°C) | P _{G(AV)} | 1.0 | W |
| Operating Junction Temperature Range | T _J | -40 to +125 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |
| RMS Isolation Voltage (t = 300 ms, R.H. ≤ 30%, T _A = 25°C) | V _{iso} | 2500 | V |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

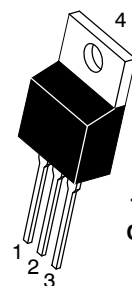
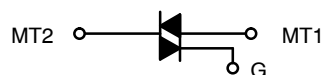
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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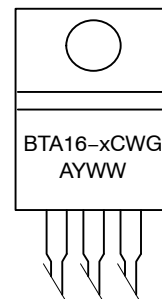
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TRIACS 16 AMPERES RMS 600 thru 800 VOLTS



TO-220AB
CASE 221A
STYLE 12

MARKING DIAGRAM



x = 6 or 8
A = Assembly Location (Optional)*
Y = Year
WW = Work Week
G = Pb-Free Package

* The Assembly Location code (A) is optional. In cases where the Assembly Location is stamped on the package the assembly code may be blank.

PIN ASSIGNMENT

| | PIN ASSIGNMENT |
|---|-----------------|
| 1 | Main Terminal 1 |
| 2 | Main Terminal 2 |
| 3 | Gate |
| 4 | No Connection |

ORDERING INFORMATION

| Device | Package | Shipping |
|---------------|-----------------------|-----------------|
| BTA16-600CW3G | TO-220AB (Pb-Free) | 50 Units / Rail |
| BTA16-800CW3G | TO-220AB (Pb-Free) | 50 Units / Rail |

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THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|-----------------|-------|----------------------|
| Thermal Resistance, Junction-to-Case (AC) | $R_{\theta JC}$ | 2.3 | $^{\circ}\text{C/W}$ |
| Junction-to-Ambient | $R_{\theta JA}$ | 60 | |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 seconds | T_L | 260 | $^{\circ}\text{C}$ |

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted; Electricals apply in both directions)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|---|--------------------|---|---|-------|----|
| Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{DRM}, V_{RRM}; \text{ Gate Open}$) | I_{DRM}, I_{RRM} | – | – | 0.005 | mA |
| $T_J = 25^{\circ}\text{C}$ | | – | – | 2.0 | |
| $T_J = 125^{\circ}\text{C}$ | | – | – | | |

ON CHARACTERISTICS

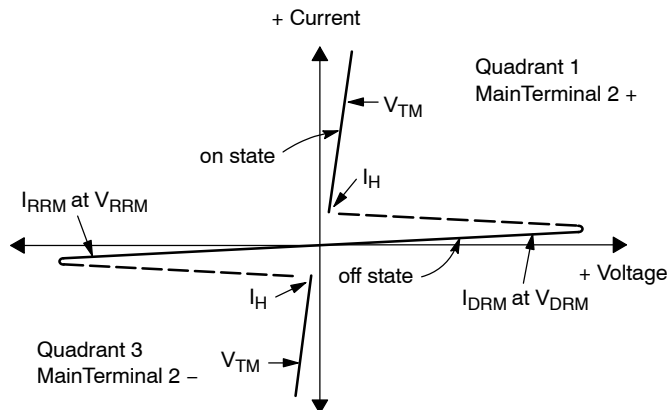
| | | | | | |
|--|----------|-----|---|------|----|
| Peak On-State Voltage (Note 2) ($I_{TM} = \pm 22.5 \text{ A Peak}$) | V_{TM} | – | – | 1.55 | V |
| Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}, R_L = 30 \Omega$) | I_{GT} | 2.0 | – | 35 | mA |
| MT2(+), G(+) | | 2.0 | – | 35 | |
| MT2(+), G(–) | | 2.0 | – | 35 | |
| MT2(–), G(–) | | 2.0 | – | 35 | |

Holding Current
(V)

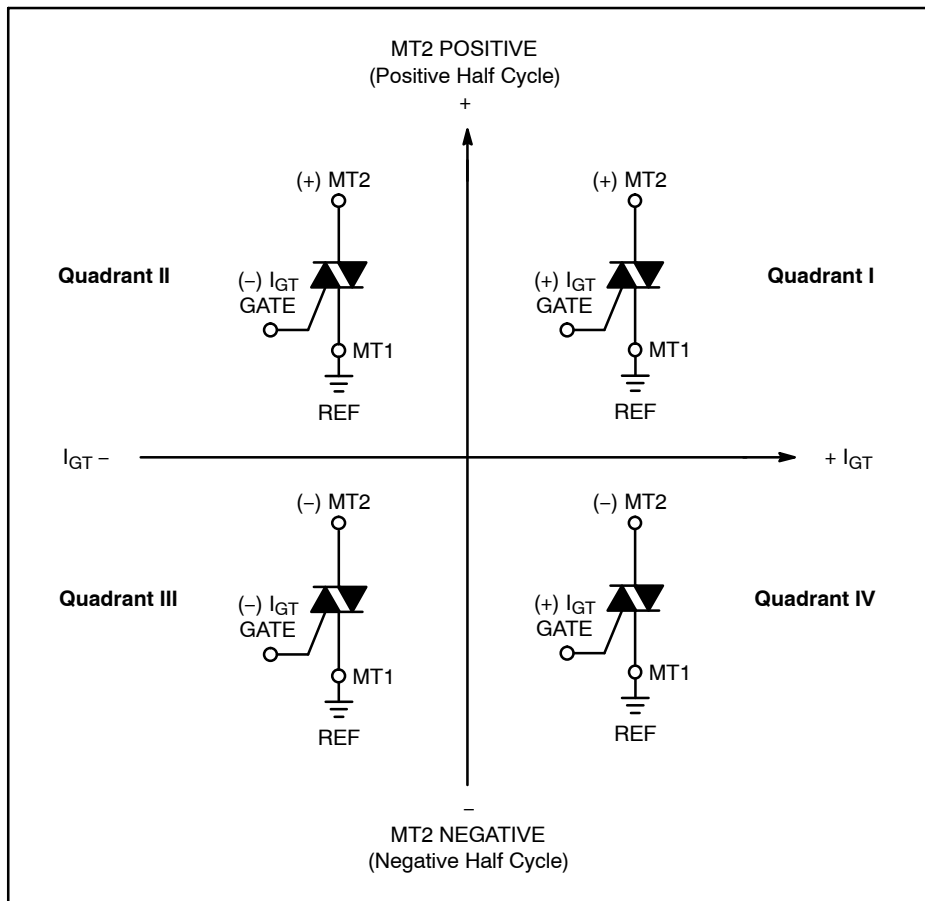
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Voltage Current Characteristic of Triacs (Bidirectional Device)

| Symbol | Parameter |
|-----------|---|
| V_{DRM} | Peak Repetitive Forward Off State Voltage |
| I_{DRM} | Peak Forward Blocking Current |
| V_{RRM} | Peak Repetitive Reverse Off State Voltage |
| I_{RRM} | Peak Reverse Blocking Current |
| V_{TM} | Maximum On State Voltage |
| I_H | Holding Current |



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

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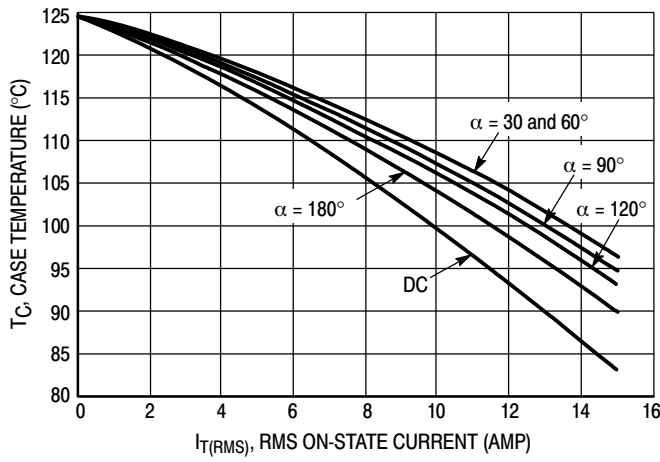


Figure 1. RMS Current Derating

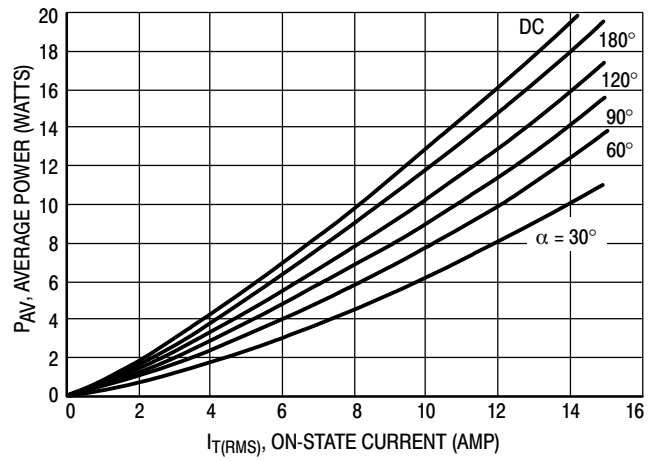


Figure 2. On-State Power Dissipation

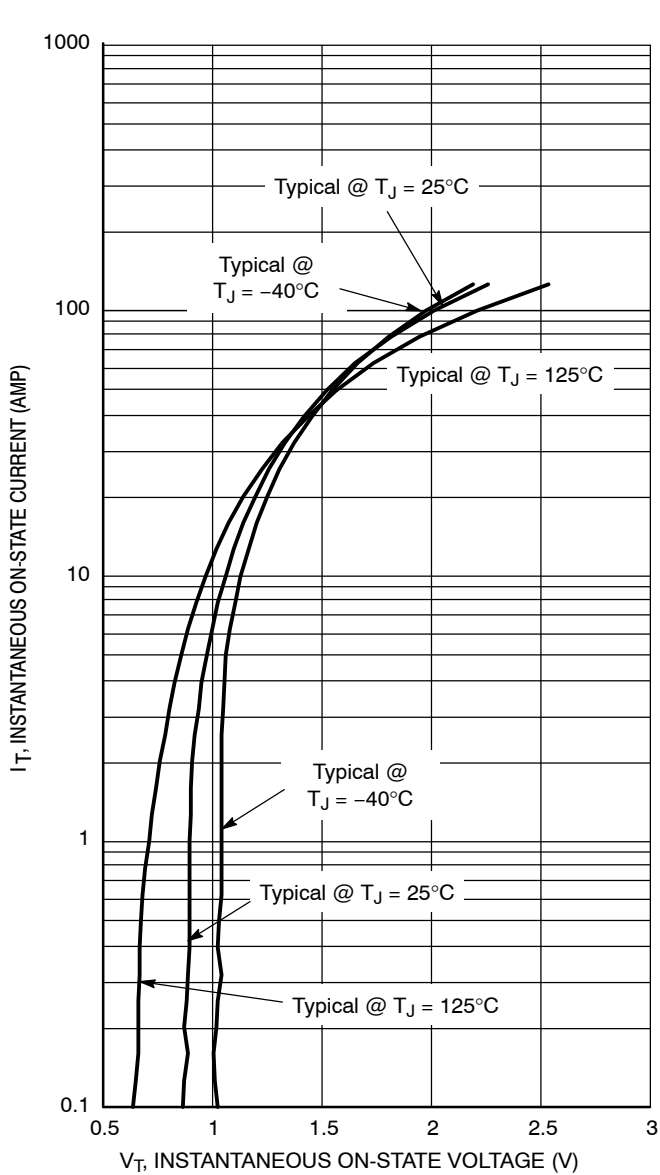


Figure 3. On-State Characteristics

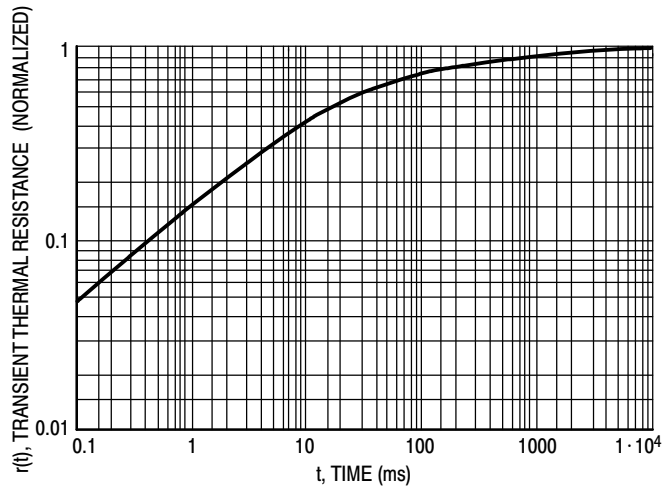


Figure 4. Thermal Response

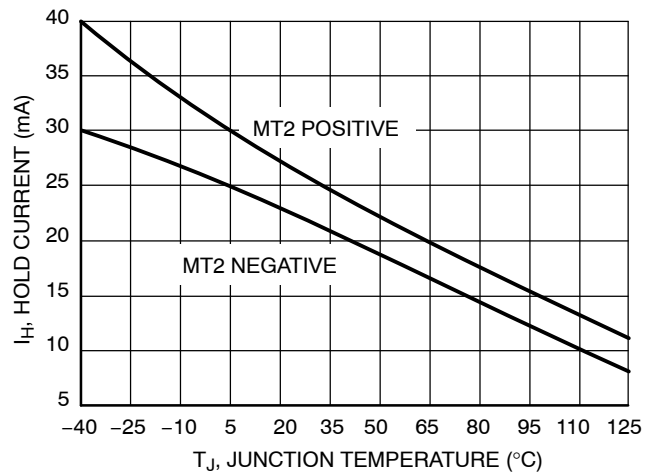


Figure 5. Hold Current Variation

Figure 6. Gate Trigger Current Variation

Figure 7. Gate Trigger Voltage Variation

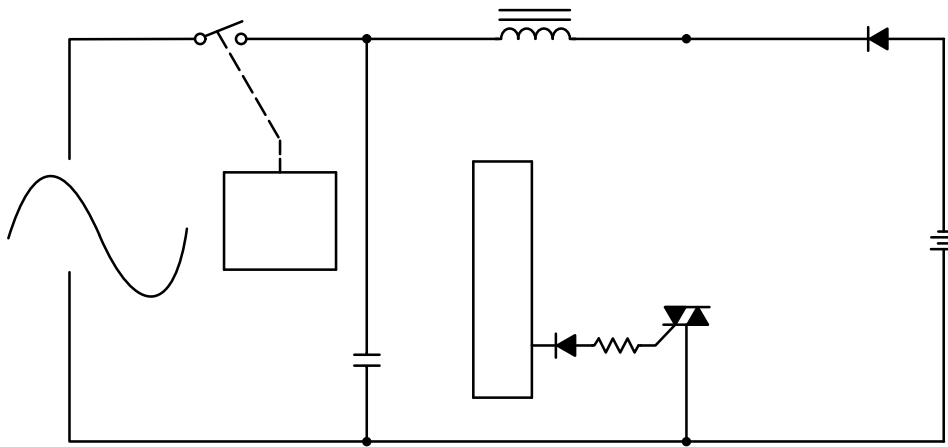
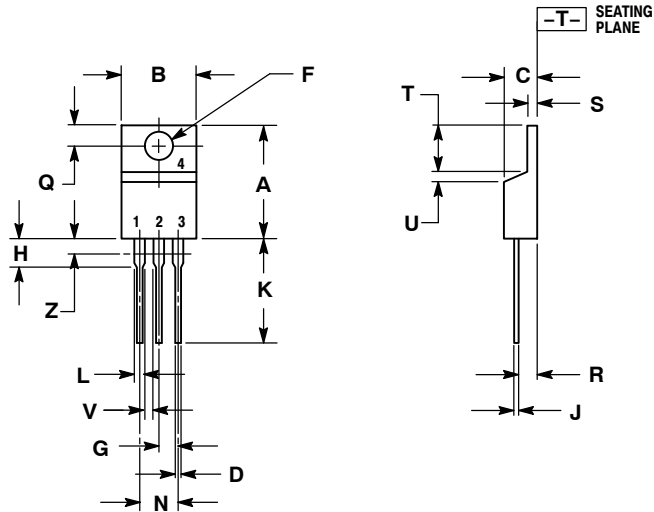


Figure 8. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current $(di/dt)_c$

BTA16-600CW3G, BTA16-800CW3G

PACKAGE DIMENSIONS

TO-220
CASE 221A-07
ISSUE AA




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.014 | 0.022 | 0.36 | 0.55 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

STYLE 12:

- PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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